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1. A method for producing a boride layer on a surface by plasma boronizing comprising:

supplying a gas mixture containing a boron-releasing gas to a treatment

chamber of a reactor;

generating a glow discharge in the reactor;

determining the amount of at least one excited boron-releasing gas product

in the glow discharge; and

selecting production parameters of the plasma generated in the treatment

chamber of the reactor so that a minimum and/or/maximum value of the determined

excited boron-releasing gas product and/or a minimum or maximum value of a relation of

one or more of the determined excited boron-releasing gas products to another glow

discharge product are maintained.

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2. A method for producing a boride layer on a surface by plasma boronizing comprising:

supplying a gas mixture containing a boron-releasing gas to a reactor; and

4 generating glow discharge in the reactor using a pulsed DC voltage source having a ratio

of voltage pulse duration to subsequent pulse pause duration which is greater than 1.1:1.

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3. A method for producing a boride layer on a surface by plasma boronizing

comprising

supplying a gas mixture containing a boron-releasing gas to a reactor; and generating a glow discharge in the reactor by applying a DC voltage in pulses having a pulse period of less than 230 μ s.

4. A method for producing a boride layer on a surface by plasma boronizing comprising:

supplying a gas mixture containing a boron-releasing gas to reactor; and generating a glow discharge in the reactor while maintaining the gas mixture at a selected low treatment temperature during a first stage to first produce a relatively thin, dense boride layer and prevent formation of halogenides which cause formation of pores, and maintaining the gas mixture at a higher temperature during in a second stage.

- 5. A method according to claim 1 wherein the glow discharge is produced using a pulsed DC voltage source having a ratio of voltage pulse duration to subsequent pulse pause duration which is greater than 1.1:1.
- 6. A method according to claim 1 wherein the glow discharge is generated by applying DC voltage pulses having a pulse period of less than 230 μ s.



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7. A method according to claim 1 wherein the method includes a first stage during which the gas mixture is maintained at a selected low temperature to prevent formation of halogonides which cause formation of pores to first produce a relatively thin, dense boride layer followed by a second stage during which the gas mixture is maintained at a higher temperature.

8. A method according to claim 2 wherein the glow discharge is generated by applying a DC voltage in pulses having a pulse period of less than 230 μ s.

A method according to claim 2 wherein the method includes a first stage during which the gas mixture is maintained at a selected low temperature to prevent formation of halogenides which cause formation of pores to first produce a relatively thin, dense boride layer, followed by a second stage during which the gas mixture is maintained at a higher temperature.

10. A method according to claim 3 wherein the method includes a first stage during which the gas mixture is maintained at a selected low temperature to prevent formation of halogenides which cause formation of pores to first produce a relatively thin, dense boride layer followed by a second stage during which the gas mixture is maintained at a higher temperature.

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11. A method according to claim 2 or claim 5 including determining the amount of excited boron-releasing gas in the reactor at least in a relative manner.

- 12. A method according to claim 11 including determining spectroscopically
- 2 the amount of excited boron-releasing gas in the reactor.
- 1 13. A method according to claim 11 including determining the amount of excited boron in the reactor at least as a function of the amount of excited boron-releasing gas in the reactor.

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14. A method according to claim 13 wherein, in order to form a minimum or maximum value of the excited boron-releasing gas content, the determined amount of the excited boron-releasing gas is set in relation to a determined amount of at least one further boron-releasing gas product.

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15. A method according to any one of claims 1-4 wherein a gas mixture is supplied which contains a boron trihalide as a boron-releasing gas in a concentration greater than about 1% by volume, along with hydrogen gas and, optionally, a noble gas.

- 16. A method according to any one of claims 1-4 wherein the glow discharge is generated by applying a pulsed DC voltage which has a ratio of the voltage pulse duration to the subsequent pulse pause duration in the range from about 1.1:1 to 5:1.
- 1 17. A method according to claim 16 wherein the ratio is in the range from about 1.5:1 to 3.5:1.
 - 18. A method according to any one of claims 1-4 wherein a pulsed BC voltage having a pulse period of less than about 210 μs is used for generating the glow discharge.
 - 19. A method according to claim 18 wherein the pulsed DC voltage has a pulse period \geq 50 μ s.
- 20. A method according to claim 19 wherein the voltage of the pulsed
 DC voltage used for generating the glow discharge in the range between about 500 volts
- 3 and about 1000 volts.
 - 21. A method according to claim 20 wherein the voltage is in the range between about 650 volts and about 800 volts.



- 22. A method according to any one of claims 1-4 wherein the reactor pressure is maintained in a low-pressure range between about 0.5 and about 15 hPa.
 - 23. A method according to claim 22 wherein the reactor pressure is
- 2 maintained in the range between about 1 and about 10 hPa.
 - 24. A method according to any one of claims 1-4 wherein the gas mixture contains a boron trihalide in a concentration of between 2% by volume and about 50% by volume.
- 1 25. A method according to claim 24 wherein the boron trihalide concentration
- 2 is between about 2% by volume and about 10% by volume.

A method according to any one of claims 1-4 wherein the gas mixture contains up to 20% by volume of a noble gas and 2% by volume to 50% by volume of boron trihalide, the remainder being hydrogen gas.

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- 27. A method according to claim 26 wherein the noble gas is argon.
- 1 28. A method according to claim 26 wherein the gas mixture contains 2% by
- 2 volume to 20% by volume of boron trihalide.

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29. A method according to any one of claims 1-4 wherein the boron-releasing gas is one of BOl₃, BF₃ and mixtures thereof.

- 30. An arrangement for producing a boride layer on a surface by plasma 2 boronizing complising: a reactor having a treatment chamber; 3 a glow discharge generator in the reactor chamber; 4 a gas supply device through which a gas mixture containing a boron-5 releasing gas is supplied to the reactor; and 6 a pulsed DC voltage source for applying pulsed DC voltage with a 7 controllable pulse width and/or pulse pause. 8
 - 31. An arrangement according to claim 30 including at least one mass flow meter for measuring and/or controlling the composition and/or the flow rate of at least one of the gases in the gas mixture.
- 1 32. An arrangement according to claim 31 including at least two flow meters
 2 for measuring and/or controlling the flow rate of the boron-releasing gas and/or hydrogen
 3 gas and/or a noble gas.

1 33. An arrangement to claim 30 including a pressure gauge for measuring the 2 pressure in the reactor. An arrangement according to claim 33 including a computer for 1 34. 2 controlling the measurement of pressure in the treatment chamber by the pressure gauge. 35. An arrangement according to claim 30 including a gas spraying device for 1 2 distributing the gas mixture into the reactor treatment chamber. An arrangement according to claim 30 including a cooled gas inlet for the 1 36. 2 boron-releasing gas. An arrangement according to claim 30 including a gas purification device 1 37. 2 connected to the treatment chamber for waste gas treatment. An arrangement according to claim 37 including a vacuum pump 1 38. 2 connected to the gas purification device. 1 39. An arrangement according to claim 30 including heating means in the 2 reactor for achieving a desired treatment temperature.